

CLAIM AMENDMENTS

Claim 1 (Cancelled).

2. (Currently Amended) ~~The A~~ method for manufacturing a semiconductor device ~~according to claim 1, wherein the mask material is~~ comprising:
forming a film to be processed on a substrate;
forming a metal film on the film to be processed;
forming a resist pattern on the metal film;
patterning the metal film using the resist pattern as a mask;
shrinking the metal film after patterning;
patterning the film to be processed using the metal film, after shrinking, as a mask;
and
removing the metal film.

3. (Currently Amended) The method for manufacturing a semiconductor device according to claim 2, ~~including forming wherein the metal film is a ruthenium film as the mask material,~~ and including removing together the mask material, ruthenium film and the resist pattern in an oxygen-containing plasma.

4. (Previously Presented) A method for manufacturing a semiconductor device comprising :
forming a film to be processed on a substrate;
forming a ruthenium film as a mask material on the film to be processed;
forming a resist pattern on the mask material;
patterning the mask material using the resist pattern as a mask;
patterning the film to be processed using the mask material, after
patterning, as a mask; and
removing the mask material.

5. (Previously Presented) The method for manufacturing a semiconductor device according to claim 4, including removing the mask material together with the resist pattern in an oxygen-containing plasma.

6. (Previously Presented) The method for manufacturing a semiconductor device according to claim 5, including removing the mask material with a metal material exposed on the substrate.